

Product Summary

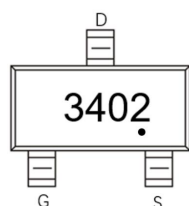
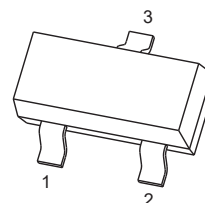
$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
30V	35mΩ@10V	4A
	38mΩ@4.5V	
	51mΩ@2.5V	

Feature

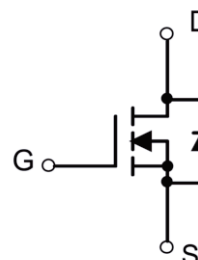
- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge

Application

- Load Switch
- DC/DC Converter
- Power Management

MARKING:

SOT-23


1. GATE
2. SOURCE
3. DRAIN

Schematic diagram

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 12	V
Continuous Drain Current ^{1,5}	$T_A = 25^\circ\text{C}$	I_D	4	A
	$T_A = 100^\circ\text{C}$		2.5	
Pulsed Drain Current ²		I_{DM}	16	A
Power Dissipation ^{4,5}		P_D	1.2	W
$T_A = 25^\circ\text{C}$				
Thermal Resistance from Junction to Ambient ⁵		$R_{\theta JA}$	103	$^\circ\text{C/W}$
Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~ +150	$^\circ\text{C}$

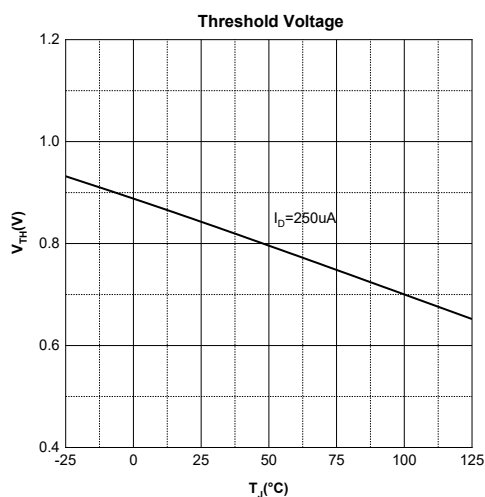
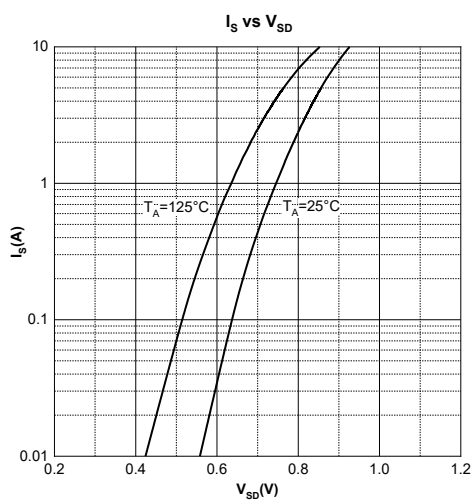
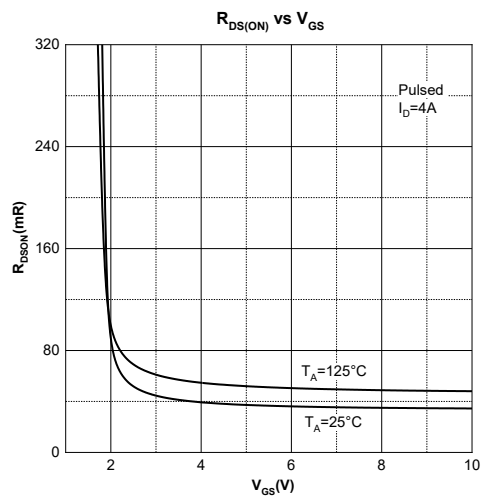
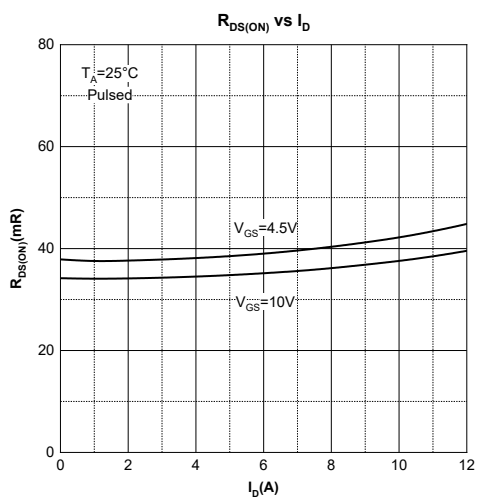
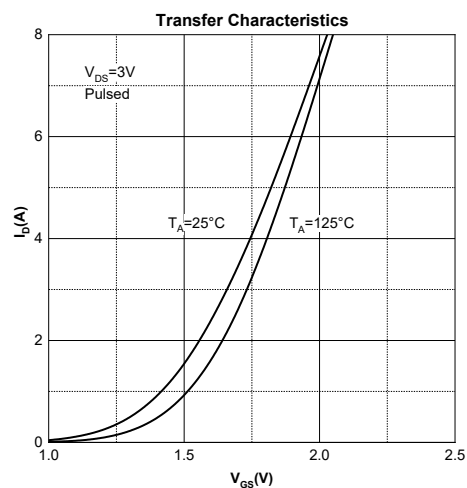
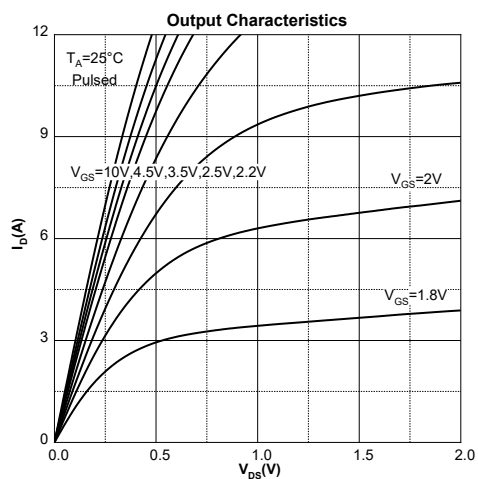
MOSFET ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

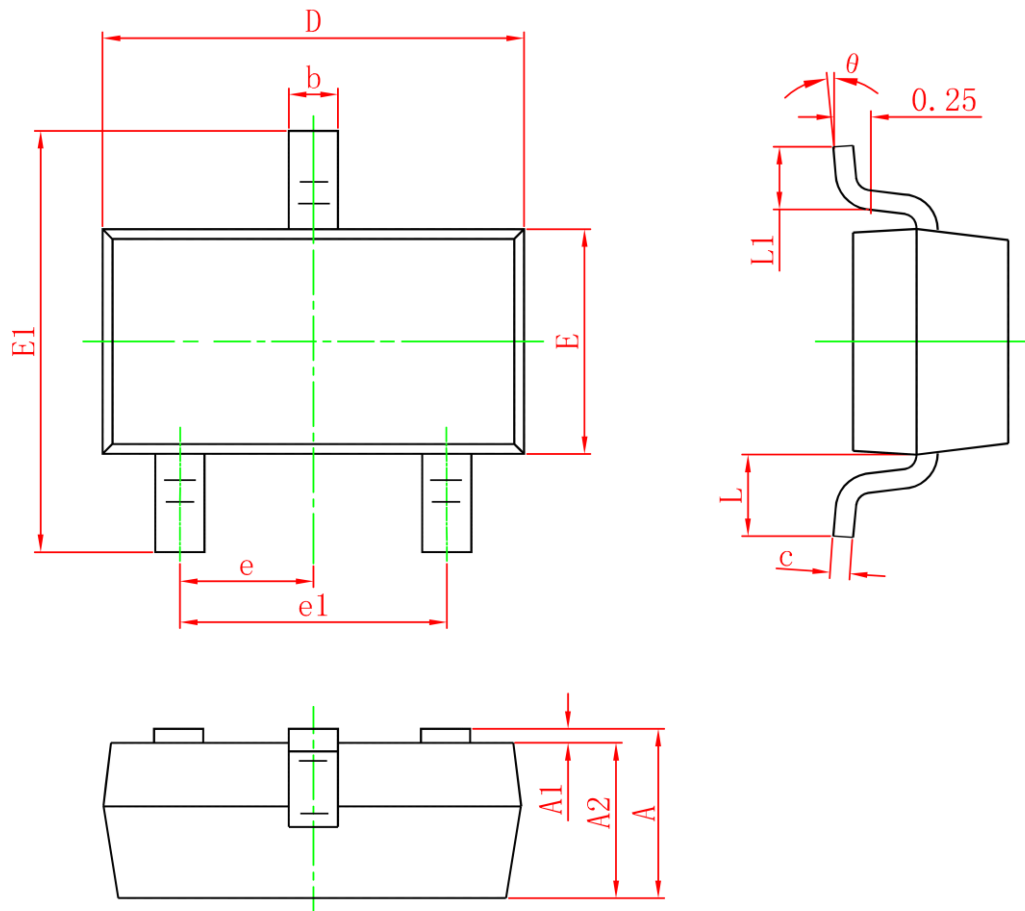
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$			± 100	nA
On Characteristics ³						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.5	0.9	1.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 4A$		35	52	m Ω
		$V_{GS} = 4.5V, I_D = 3A$		38	65	
		$V_{GS} = 2.5V, I_D = 2A$		51	85	
Dynamic Characteristics ⁴						
Input Capacitance	C_{iss}	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$		412		pF
Output Capacitance	C_{oss}			26		
Reverse Transfer Capacitance	C_{rss}			22		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		1.7		Ω
Switching Characteristics ⁴						
Total Gate Charge	Q_g	$V_{DS} = 15V, V_{GS} = 10V, I_D = 4A$		11		nC
Gate-Source Charge	Q_{gs}			1.0		
Gate-Drain Charge	Q_{gd}			1.7		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10V, V_{GS} = 4.5V, I_D = 2A,$ $R_G = 3\Omega$		4		ns
Turn-On Rise Time	t_r			14		
Turn-Off Delay Time	$t_{d(off)}$			40		
Turn-Off Fall Time	t_f			17		
Source-Drain Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	$V_{GS} = 0V, I_S = 1A$			1.2	V

Notes :

- 1.The maximum current rating is limited by package.
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 4.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.
- 5.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics



SOT-23 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0	0.100	0	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.150	1.500	0.045	0.059
E1	2.250	2.650	0.089	0.104
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.